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## Correction: Composition control of conformal crystalline GeSbTe films by atomic layer deposition supercycles and tellurization annealing

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The authors regret errors in affiliation *b* of the coauthors in the published article, from which the words "Samsung Electronics Co., Ltd." were unfortunately omitted. The correct affiliation list is as shown here.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.



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